Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{i(max)} = 150$ °C).

2. Features and benefits

- High bidirectional blocking voltage capability
- · High junction operating temperature capability
- · High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

3. Applications

- Capacitive Discharge Ignition (CDI)
- · Crowbar protection
- · Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{RRM}	repetitive peak reverse voltage			-	-	800	V	
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 1</u>		-	-	12.7	A	
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 129 ^{\circ}\text{C}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$		-	-	20	A	
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	-	210	A	
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	-	231	A	
Tj	junction temperature			-	-	150	°C	
Static chara	Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		-	4.5	32	mA	
Dynamic characteristics								

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
D.	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs

5. Pinning information

Table 2. Pinning information

	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	А - К
2	Α	anode	├ ○ ┤	G sym037
3	G	gate		cymce.
mb	Α	mounting base; connected to anode	TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
TYN20-800T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

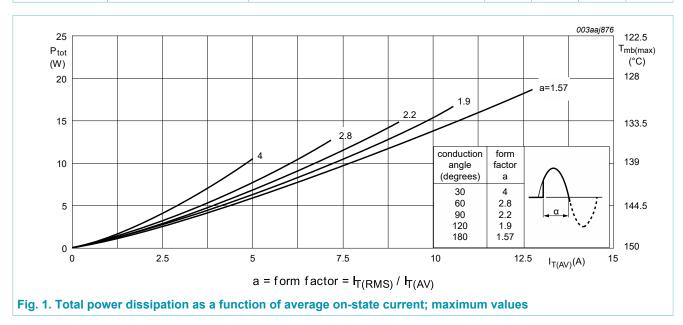
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 1</u>	-	12.7	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 129 ^{\circ}\text{C}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	20	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5	-	210	Α
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	231	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	220.5	A²s
dl _T /dt	rate of rise of on-state current	I _G = 70 mA	-	100	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C



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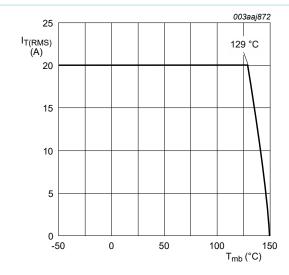


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

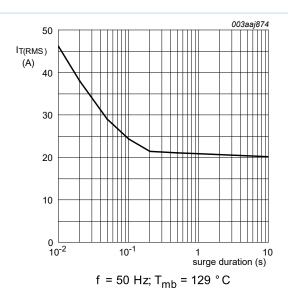


Fig. 3. RMS on-state current as a function of surge duration; maximum values

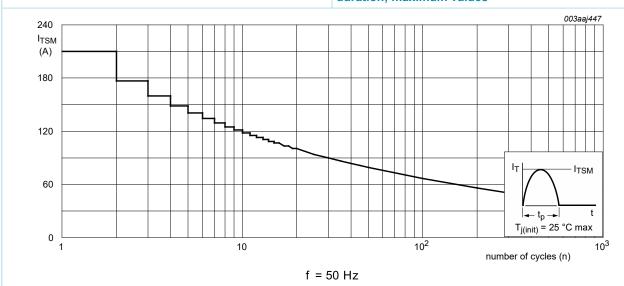
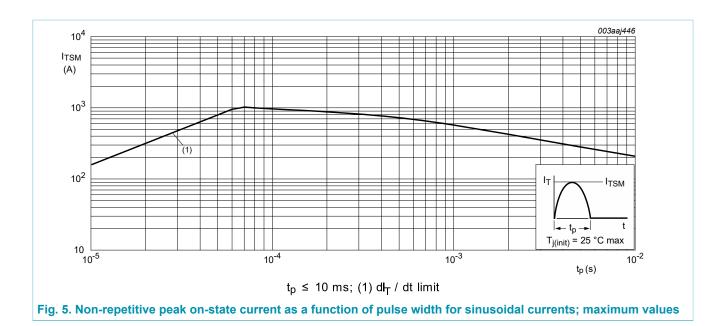


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

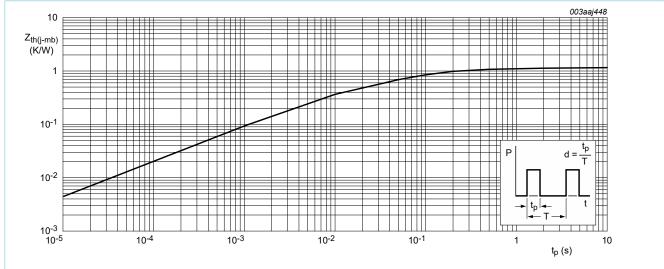


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u>	-	4.5	32	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	21	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	16	40	mA
V _T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.7	1.3	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 11	0.2	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 150 °C	-	0.2	1	mA
I _R	reverse current	V _R = 800 V; T _j = 150 °C	-	0.2	1	mA
Dynamic ch	naracteristics				'	
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 150 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 800 V; I_G = 100 mA; dI_G/dt = 5 A/ μ s; T_j = 25 °C	-	-	2	μs
t _q	commutated turn-off time	V_{DM} = 536 V; T_j = 125 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	-	70	-	μs

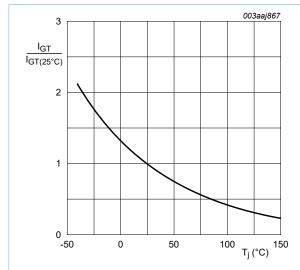


Fig. 7. Normalized gate trigger current as a function of junction temperature

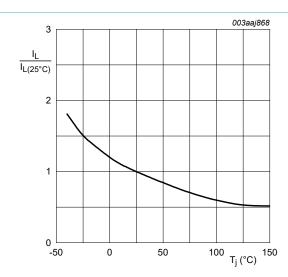


Fig. 8. Normalized latching current as a function of junction temperature

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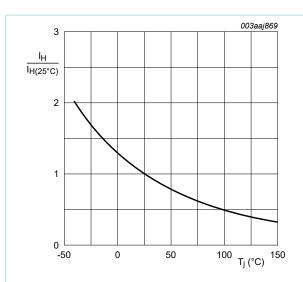
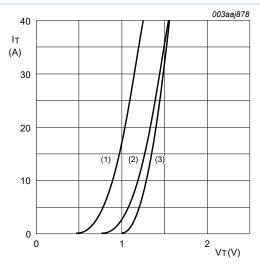


Fig. 9. Normalized holding current as a function of junction temperature



 V_0 = 1.0485 V; R_s = 0.0133 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

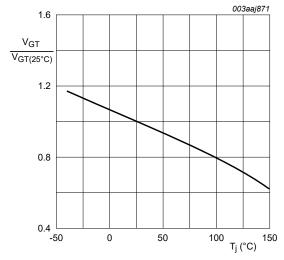
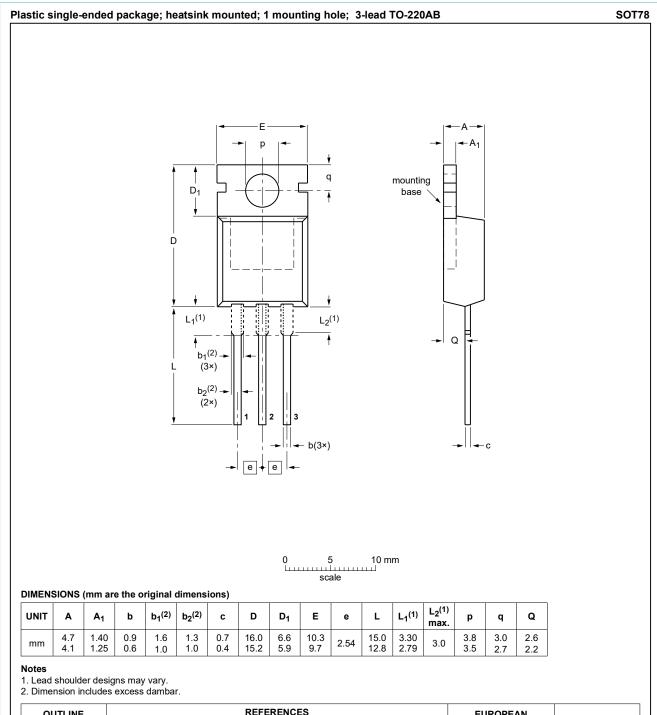


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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10. Package outline



		ISSUE DATE
VERSION IEC JEDEC JEITA	PROJECTION	1330E DATE
SOT78 3-lead TO-220AB SC-46	$\bigoplus \bigoplus$	08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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